

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

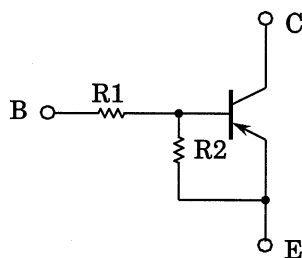
RN2207, RN2208, RN2209

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

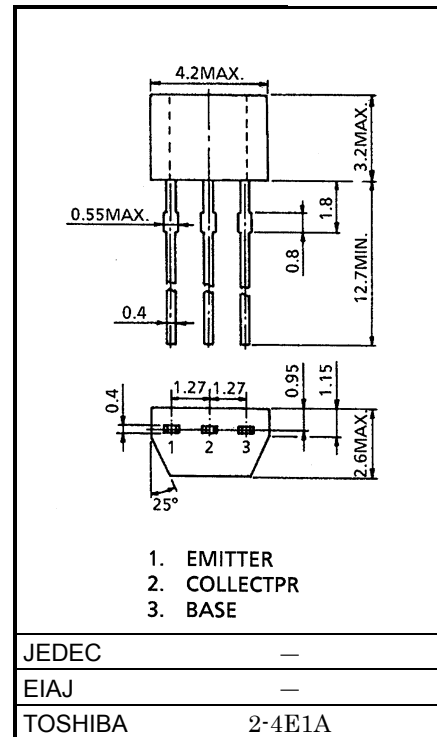
Unit in mm

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1207~RN1209

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2207	10	47
RN2208	22	47
RN2209	47	22



Weight: 0.13g

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-6	V
		-7	
		-15	
Collector current	I_C	-100	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

961001EAA1

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit				
Collector cut-off current		I _{CBO}	—	V _{CB} = -50V, I _E = 0	—	—	-100	nA				
		I _{CEO}	—	V _{CE} = -50V, I _B = 0	—	—	-500					
Emitter cut-off current		RN2207	I _{EBO}	—	V _{EB} = -6V, I _C = 0	-0.081	—	-0.15				
		RN2208							V _{EB} = -7V, I _C = 0	-0.078	—	-0.145
		RN2209							V _{EB} = -15V, I _C = 0	-0.167	—	-0.311
DC current gain		RN2207	h _{FE}	—	V _{CE} = -5V, I _C = -10mA	80	—	—				
		RN2208							80	—	—	
		RN2209							70	—	—	
Collector-emitter saturation voltage		V _{CE(sat)}	—	I _C = -5mA, I _B = -0.25mA	—	-0.1	-0.3	V				
Input voltage (ON)		RN2207	V _{I(ON)}	—	V _{CE} = -0.2V, I _C = -5mA	-0.7	—	-1.8				
		RN2208							-1.0	—	-2.6	
		RN2209							-2.2	—	-5.8	
Input voltage (OFF)		RN2207	V _{I(OFF)}	—	V _{CE} = -5V, I _C = -0.1mA	-0.5	—	-1.0				
		RN2208							-0.6	—	-1.16	
		RN2209							-1.5	—	-2.6	
Translation frequency		f _T	—	V _{CE} = -10V, I _C = -5mA	—	200	—	MHz				
Collector output capacitance		C _{ob}	—	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3	6	pF				
Input resistor		RN2207	R1	—	—	7	10	13				
		RN2208							15.4	22	28.6	
		RN2209							32.9	47	61.1	
Resistor ratio		RN2207	R1/R2	—	—	0.191	0.213	0.232				
		RN2208							0.421	0.468	0.515	
		RN2209							1.92	2.14	2.35	

